

NPN General Purpose Amplifier

This device is designed for low noise, high gain, general purpose amplifier applications at collector currents from 1.0 μ A to 50 mA. Sourced from Process 07.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter		Value	Units
V _{CEO}	Collector-Emitter Voltage	BC846 series BC847 series	65 45	V V
V _{CES}	Collector-Base Voltage	BC846 series BC847 series	80 50	V V
V _{EBO}	Emitter-Base Voltage		6.0	V
I _C	Collector Current - Continuous		100	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range		-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах	Units
		*BC846 / BC847	
P _D	Total Device Dissipation	325	mW
	Derate above 25°C	2.8	mW/∘C
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

*Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

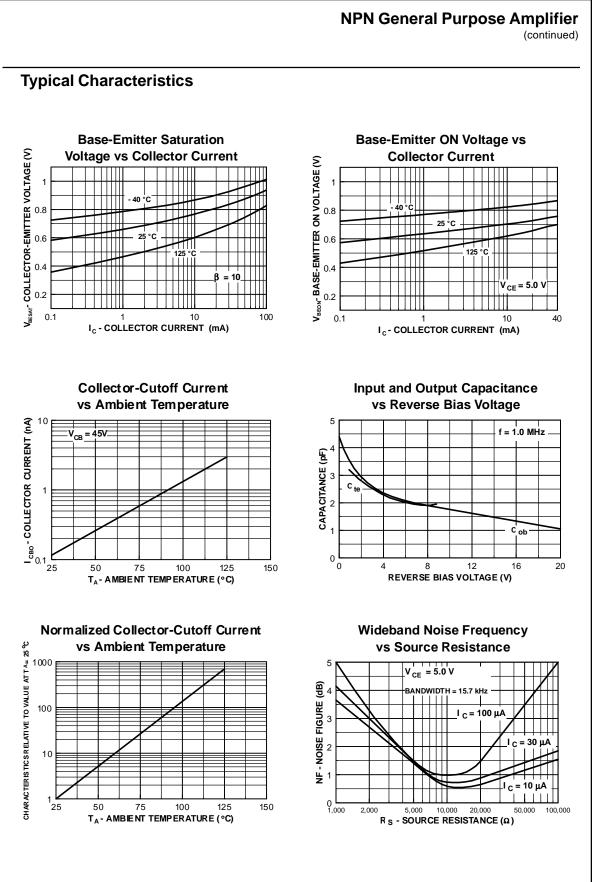
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NPN General Purpose Amplifier

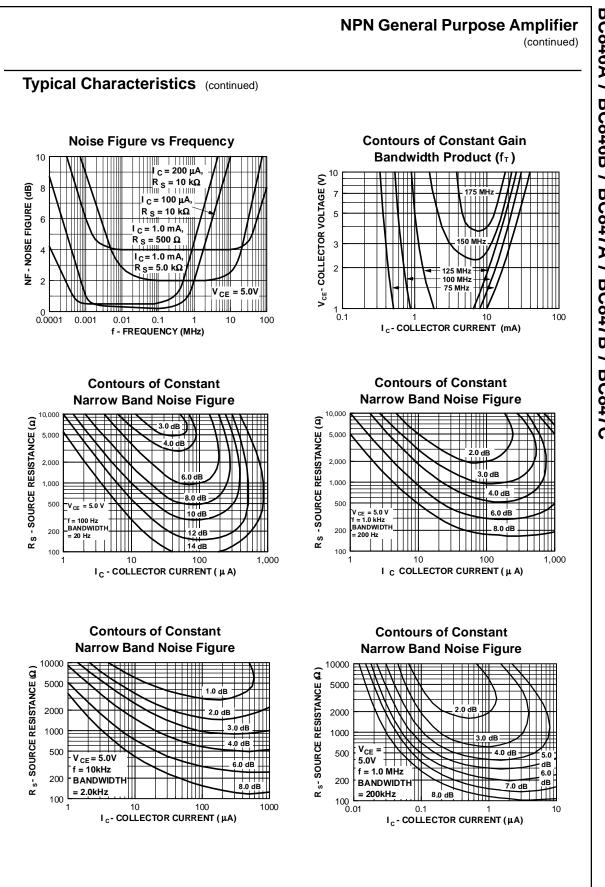
100

	Parameter	Test Conditions	Min	Мах	Units
OFF CHA	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$ 846A / B	65		V
N/	Voltage	847A/B	45		V
V _{(BR)CES}	Collector-Base Breakdown Voltage	$I_{C} = 10 \ \mu A, I_{E} = 0$ 846A / B 847A / B	80 50		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \ \mu {\rm A}, \ I_{\rm C} = 0$	6.0		V
сво	Collector-Cutoff Current	V _{CB} = 30 V		15	nA
		V _{CB} = 30 V, T _A = 150°C		5.0	μA
ON CHAR	ACTERISTICS				
h _{FE}	DC Current Gain	$I_{C} = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$			
		846A / 847A	110	220	
		846B / 847B 847C	200 420	450 800	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0.5 \text{ mA}$		0.25	V
	_	$I_{\rm C} = 100 \text{ mA}, I_{\rm B} = 5.0 \text{ mA}$		0.6	V
V _{BE(on)}	Base-Emitter On Voltage	$I_{C} = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$	0.58	0.70 0.77	V V
	GNAL CHARACTERISTICS	1			
т	Current Gain - Bandwidth Product	$I_{C} = 10 \text{ mA}, V_{CE} = 5.0,$ f = 100 MHz	100		MHz
C _{obo}	Output Capacitance	V _{CB} = 10 V, f = 1.0 MHz		4.5	pF
NF	Noise Figure	$I_{C} = 0.2 \text{ mA}, V_{CE} = 5.0,$		10	dB
		R _S = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz			
Туріса	al Characteristics				
Туріса	al Characteristics				
	al Characteristics Typical Pulsed Current Gain	Collector-E S Voltage vs 0.3 $\beta = 10$ $\beta = 10$ 0.2			

h _E- TYPICAL PULSED V_{cESAT}- COLLECTOR-EMIT 0 0.02 0 0 0.02 Ш 600 25 °C 400 25 40 °C||||| 200 0 .01 0.03 0.1 0.3 1 3 10 Ic - COLLECTOR CURRENT (mA) 30 100 1 10 I_c-COLLECTOR CURRENT (mA) 0.1



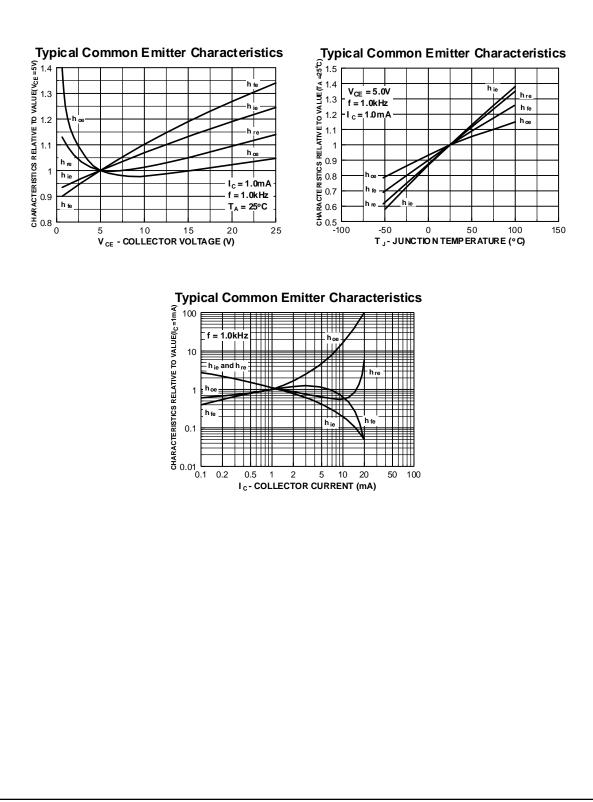
BC846A / BC846B / BC847A / BC847B / BC847C





NPN General Purpose Amplifier (continued)

Typical Common Emitter Characteristics (f = 1.0 kHz)



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